Abstracts

A 6 Watt 6 GHz GaAsFET Power Module with GaAs Matching Circuits

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F.M. Magalhaes, J.P. Beccone, J.C. Irvin, S.J. Perelli and W.O. Schlosser. "A 6 Watt 6 GHz GaAsFET Power Module with GaAs Matching Circuits." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 437-438.

A GaAs matched FET (M-FET) technology has been developed which incorporates separate GaAs matching chips and GaAsFETs within a small hermetic package. By using two separately matched 6 mm FET chips in the design, we have achieved 6.3 watts of output power with 9 dB associated gain at 6 GHz.

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